

# 2.5V Drive Nch MOSFET

# RU1L002SN

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Low voltage drive (2.5V drive).
- 3) Small package (UMT3F).

# Application

Switching

# Packaging specifications

|          | Package                      | Taping |  |
|----------|------------------------------|--------|--|
| Type     | Code                         | TCL    |  |
|          | Basic ordering unit (pieces) | 3000   |  |
| RU1L002S | 0                            |        |  |

# ● Absolute maximum ratings (Ta = 25°C)

| Paramet                      | Symbol     | Limits             | Unit        |    |
|------------------------------|------------|--------------------|-------------|----|
| Drain-source voltage         |            | $V_{DSS}$          | 60          | V  |
| Gate-source voltage          |            | $V_{GSS}$          | ±20         | V  |
| Drain current                | Continuous | I <sub>D</sub>     | ±250        | mA |
|                              | Pulsed     | I <sub>DP</sub> *1 | ±1          | Α  |
| Source current               | Continuous | I <sub>S</sub>     | 125         | mA |
| (Body Diode)                 | Pulsed     | I <sub>SP</sub> *1 | 1           | Α  |
| Power dissipation            |            | P <sub>D</sub> *2  | 200         | mW |
| Channel temperature          |            | Tch                | 150         | °C |
| Range of storage temperature |            | Tstg               | -55 to +150 | °C |

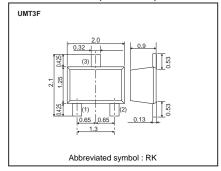
<sup>\*1</sup> Pw≤10µs, Duty cycle≤1%

# Thermal resistance

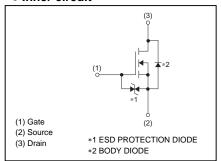
| Parameter          | Symbol     | Limits | Unit |
|--------------------|------------|--------|------|
| Channel to Ambient | Rth (ch-a) | 625    | °C/W |

<sup>\*</sup> Each terminal mounted on a recommended land

#### • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*2</sup> Each terminal mounted on a recommended land

# ● Electrical characteristics (Ta = 25°C)

| Parameter                       | Symbol                | Min. | Тур. | Max. | Unit | Conditions                                   |
|---------------------------------|-----------------------|------|------|------|------|--|
| Gate-source leakage             | $I_{GSS}$             |      | -    | ±10  | μA   | $V_{GS}=\pm20V$ , $V_{DS}=0V$                |
| Drain-source breakdown voltage  | $V_{(BR)DSS}$         | 60   | -    | -    | V    | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V     |
| Zero gate voltage drain current | I <sub>DSS</sub>      |      | -    | 1    | μA   | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V    |
| Gate threshold voltage          | V <sub>GS (th)</sub>  | 1.0  | -    | 2.3  | V    | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA    |
|                                 |                       |      | 1.7  | 2.4  | Ω    | I <sub>D</sub> =250mA, V <sub>GS</sub> =10V  |
| Static drain-source on-state    | R *                   | -    | 2.1  | 3.0  |      | I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V |
| resistance                      | R <sub>DS (on)</sub>  | -    | 2.3  | 3.2  |      | I <sub>D</sub> =250mA, V <sub>GS</sub> =4.0V |
|                                 |                       | 1    | 3.0  | 12.0 |      | I <sub>D</sub> =10mA, V <sub>GS</sub> =2.5V  |
| Forward transfer admittance     | IY <sub>fs</sub> I*   | 0.25 | -    | -    | S    | V <sub>DS</sub> =10V, I <sub>D</sub> =250mA  |
| Input capacitance               | C <sub>iss</sub>      | 1    | 15   | -    | pF   | V <sub>DS</sub> =25V                         |
| Output capacitance              | $C_{oss}$             | -    | 4.5  | -    | pF   | V <sub>GS</sub> =0V                          |
| Reverse transfer capacitance    | $C_{rss}$             | -    | 2.0  | -    | pF   | f=1MHz                                       |
| Turn-on delay time              | t <sub>d(on)</sub> *  | -    | 3.5  | -    | ns   | V <sub>DD</sub> ≒30V, I <sub>D</sub> =100mA  |
| Rise time                       | t <sub>r</sub> *      | -    | 5    | -    | ns   | V <sub>GS</sub> =10V                         |
| Turn-off delay time             | t <sub>d(off)</sub> * | -    | 18   | -    | ns   |  |
| Fall time                       | t <sub>f</sub> *      | -    | 28   | -    | ns   |  |

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

| Parameter       | Symbol            | Min. | Тур. | Max. | Unit | Conditions                 |
|-----------------|-------------------|------|------|------|------|----------------------------|
| Forward Voltage | V <sub>SD</sub> * | -    | -    | 1.2  | V    | $I_s$ =250mA, $V_{GS}$ =0V |

<sup>\*</sup>Pulsed

#### ●Electrical characteristic curves (Ta=25°C)

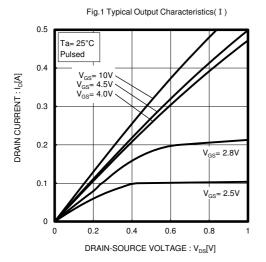


Fig.3 Typical Transfer Characteristics

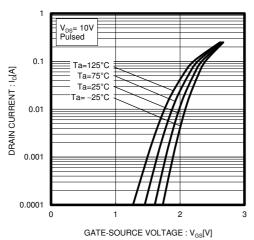
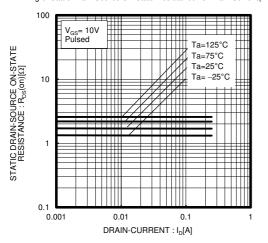


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )



0.5

V<sub>GS</sub>= 10V
V<sub>GS</sub>= 4.5V
V<sub>GS</sub>= 4.5V
V<sub>GS</sub>= 4.0V

V<sub>GS</sub>= 2.8V

0.1

0

Fig.2 Typical Output Characteristics(  ${\rm I\hspace{-.1em}I}$  )

DRAIN-SOURCE VOLTAGE :  $V_{DS}[V]$ 

10

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

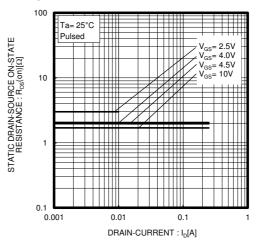


Fig.6 Static Drain-Source On-State Resistance vs. Drain  $Current({\rm I\hspace{-.1em}I\hspace{-.1em}I})$ 

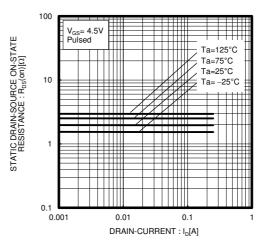


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

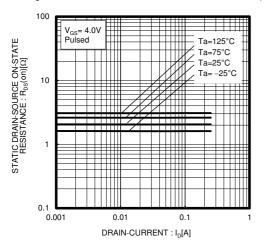


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current( $\mathbb{IV}$ )

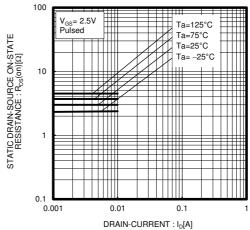


Fig.9 Forward Transfer Admittance vs. Drain Current

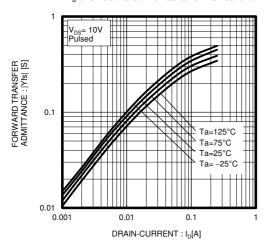


Fig.10 Reverse Drain Current vs. Sourse-Drain Voltage

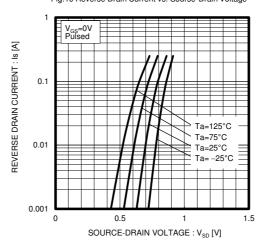


Fig.11 Static Drain-Source On-State Resistance vs. Gate Source Voltage

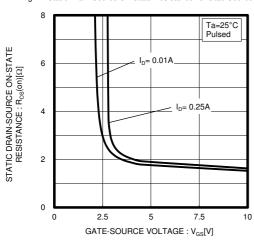
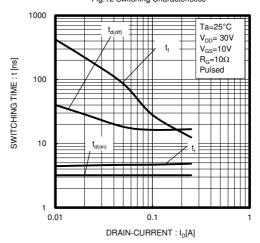
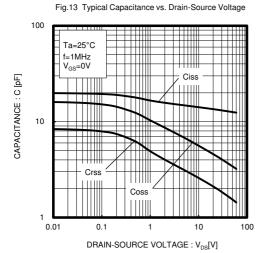


Fig.12 Switching Characteristics





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Data Sheet

# Measurement circuits

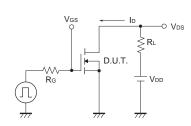


Fig.1-1 Switching Time Measurement Circuit

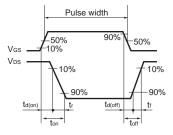


Fig.1-2 Switching Waveforms

#### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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